

74LVC1G58

Low-power configurable multiple function gate

Rev. 01 — 15 September 2004

Product data sheet

1. General description

The 74LVC1G58 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC1G58 provides configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XOR, inverter and buffer. All inputs can be connected to V_{CC} or GND.

The three inputs (A, B and C) are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The gate switches at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the hysteresis voltage V_H .

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8B/JESD36 (2.7 V to 3.6 V).
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-B exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V.
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C.

PHILIPS

3. Quick reference data

Table 1: Quick reference data

$GND = 0\text{ V}$; $T_{amb} = 25\text{ °C}$; $t_r = t_f \leq 2.5\text{ ns}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PHL} , t_{PLH}	propagation delay input A, B and C to output Y	$V_{CC} = 1.8\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 1\text{ k}\Omega$	-	6	-	ns
		$V_{CC} = 2.5\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 500\ \Omega$	-	3.5	-	ns
		$V_{CC} = 2.7\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\ \Omega$	-	4.2	-	ns
		$V_{CC} = 3.3\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\ \Omega$	-	3.8	-	ns
		$V_{CC} = 5.0\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\ \Omega$	-	3.0	-	ns
C_I	input capacitance		-	2.5	-	pF
C_{PD}	power dissipation capacitance per buffer	$V_{CC} = 3.3\text{ V}$	[1][2]	20	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] The condition is $V_I = GND$ to V_{CC} .

4. Ordering information

Table 2: Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G58GW	-40 °C to +125 °C	SC-88	plastic surface mounted package; 6 leads	SOT363
74LVC1G58GV	-40 °C to +125 °C	SC-74	plastic surface mounted package; 6 leads	SOT457
74LVC1G58GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5\text{ mm}$	SOT886

5. Marking

Table 3: Marking

Type number	Marking code
74LVC1G58GW	YK
74LVC1G58GV	V58
74LVC1G58GM	YK

6. Functional diagram

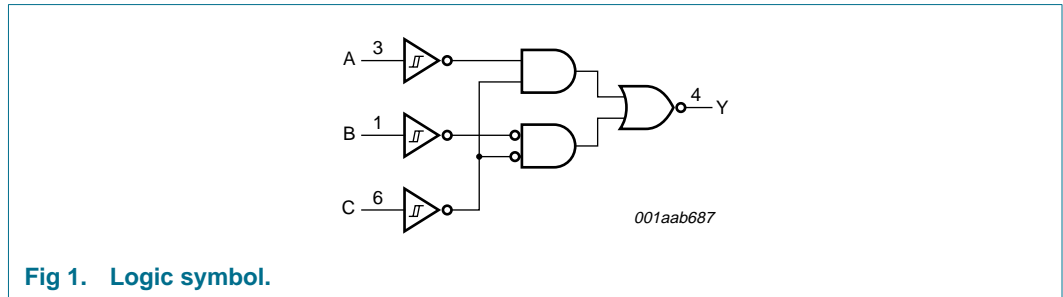


Fig 1. Logic symbol.

7. Pinning information

7.1 Pinning

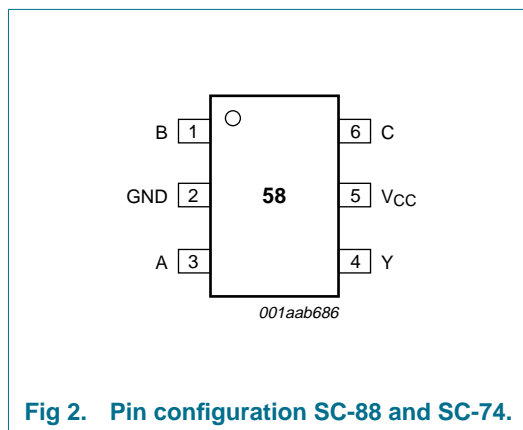


Fig 2. Pin configuration SC-88 and SC-74.

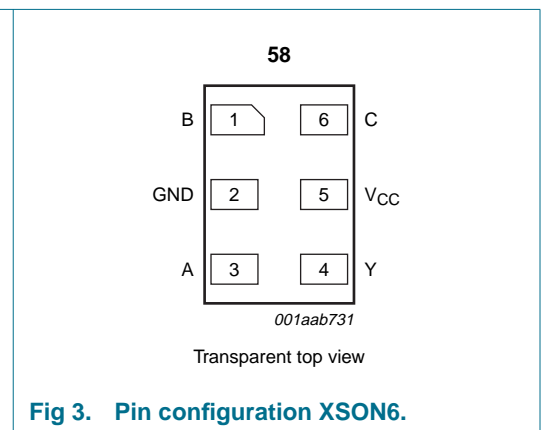


Fig 3. Pin configuration XSON6.

7.2 Pin description

Table 4: Pin description

Symbol	Pin	Description
B	1	data input B
GND	2	ground (0 V)
A	3	data input A
Y	4	data output Y
V _{CC}	5	supply voltage
C	6	data input C

8. Functional description

8.1 Function table

Table 5: Function table [1]

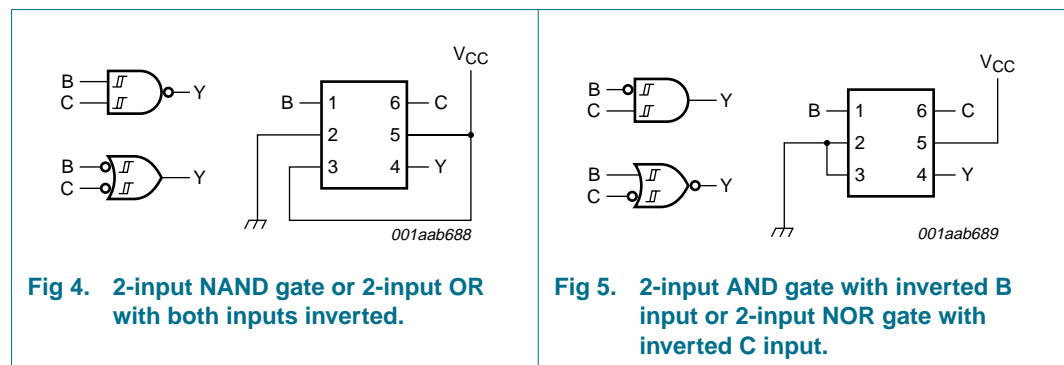
Inputs			Output
C	B	A	Y
L	L	L	L
L	L	H	H
L	H	L	L
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	L
H	H	H	L

[1] H = HIGH voltage level;
L = LOW voltage level.

8.2 Logic configurations

Table 6: Function selection table

Logic function	Figure
2-input NAND	see Figure 4
2-input NAND with both inputs inverted	see Figure 7
2-input AND with inverted input	see Figure 5 and 6
2-input NOR with inverted input	see Figure 5 and 6
2-input OR	see Figure 7
2-input OR with both inputs inverted	see Figure 4
2-input XOR	see Figure 8
Buffer	see Figure 9
Inverter	see Figure 10



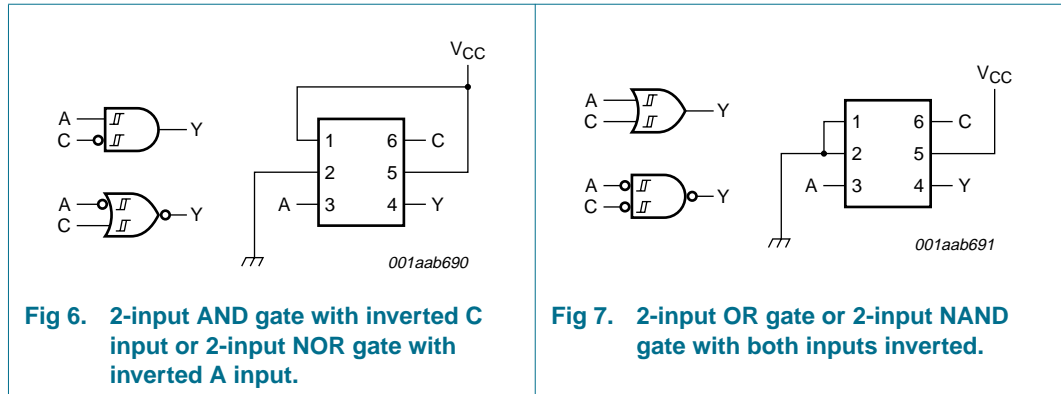


Fig 6. 2-input AND gate with inverted C input or 2-input NOR gate with inverted A input.

Fig 7. 2-input OR gate or 2-input NAND gate with both inputs inverted.

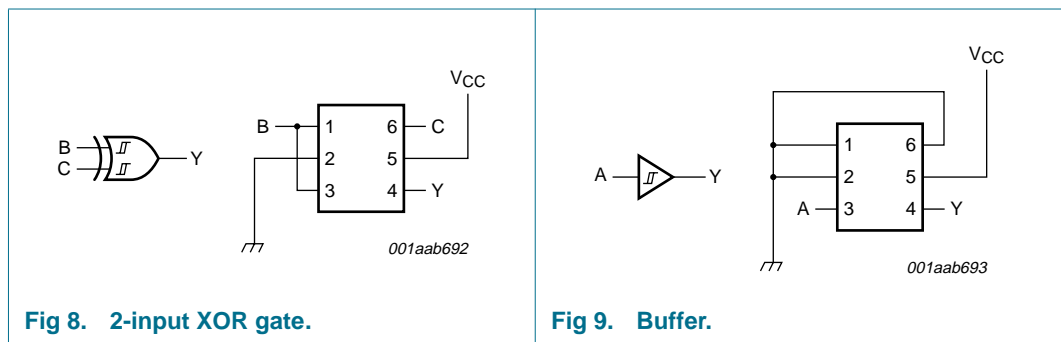


Fig 8. 2-input XOR gate.

Fig 9. Buffer.

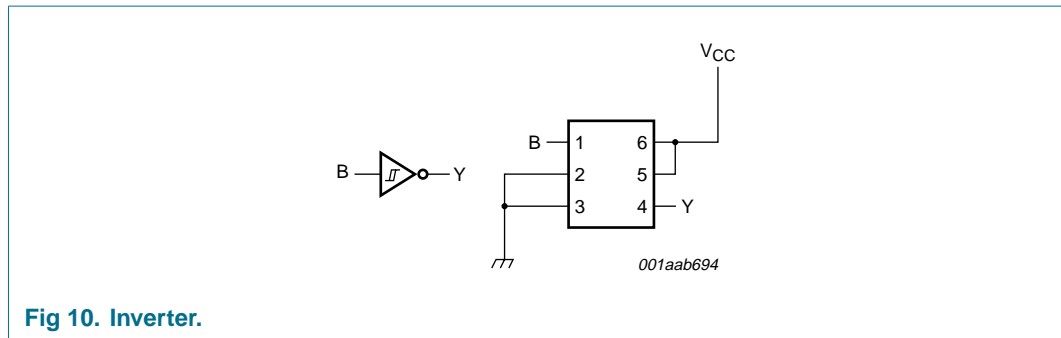


Fig 10. Inverter.

9. Limiting values

Table 7: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$ V	-	-50	mA
V_I	input voltage		[1] -0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
V_O	output voltage	active mode	[1][2] -0.5	+6.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
I_O	output source or sink current	$V_O = 0$ V to V_{CC}	-	±50	mA

Table 7: Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{CC}, I_{GND}	V_{CC} or GND current		-	± 100	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	power dissipation	$T_{amb} = -40\text{ °C to }+125\text{ °C}$	-	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0\text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

10. Recommended operating conditions

Table 8: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	active mode	0	-	V_{CC}	V
		$V_{CC} = 0\text{ V}$; Power-down mode	0	-	5.5	V
T_{amb}	operating ambient temperature		-40	-	+125	°C

11. Static characteristics

Table 9: Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1]						
V_{OL}	LOW-level output voltage	$V_I = V_{CC}$ or GND				
		$I_O = 100\text{ }\mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	-	-	0.1	V
		$I_O = 4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	-	-	0.45	V
		$I_O = 8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	-	-	0.3	V
		$I_O = 12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	-	-	0.4	V
		$I_O = 24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	-	-	0.55	V
		$I_O = 32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	-	0.55	V
V_{OH}	HIGH-level output voltage	$V_I = V_{CC}$ or GND				
		$I_O = -100\text{ }\mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	$V_{CC} - 0.1$	-	-	V
		$I_O = -4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	1.2	-	-	V
		$I_O = -8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	1.9	-	-	V
		$I_O = -12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	2.2	-	-	V
		$I_O = -24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	2.3	-	-	V
		$I_O = -32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	3.8	-	-	V
I_{LI}	input leakage current	$V_I = 5.5\text{ V}$ or GND; $V_{CC} = 3.6\text{ V}$	-	± 0.1	± 5	μA

Table 9: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{off}	power OFF leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	± 0.1	± 10	μ A
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	0.1	10	μ A
ΔI_{CC}	additional quiescent supply current per pin	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	5	500	μ A
C_I	input capacitance		-	2.5	-	pF
$T_{amb} = -40$ °C to $+125$ °C						
V_{OL}	LOW-level output voltage	$V_I = V_{CC}$ or GND				
		$I_O = 100$ μ A; $V_{CC} = 1.65$ V to 5.5 V	-	-	0.1	V
		$I_O = 4$ mA; $V_{CC} = 1.65$ V	-	-	0.7	V
		$I_O = 8$ mA; $V_{CC} = 2.3$ V	-	-	0.45	V
		$I_O = 12$ mA; $V_{CC} = 2.7$ V	-	-	0.6	V
		$I_O = 24$ mA; $V_{CC} = 3.0$ V	-	-	0.8	V
		$I_O = 32$ mA; $V_{CC} = 4.5$ V	-	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{CC}$ or GND				
		$I_O = -100$ μ A; $V_{CC} = 1.65$ V to 5.5 V	$V_{CC} - 0.1$	-	-	V
		$I_O = -4$ mA; $V_{CC} = 1.65$ V	0.95	-	-	V
		$I_O = -8$ mA; $V_{CC} = 2.3$ V	1.7	-	-	V
		$I_O = -12$ mA; $V_{CC} = 2.7$ V	1.9	-	-	V
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	2.0	-	-	V
		$I_O = -32$ mA; $V_{CC} = 4.5$ V	3.4	-	-	V
I_{LI}	input leakage current	$V_I = 5.5$ V or GND; $V_{CC} = 3.6$ V	-	-	± 100	μ A
I_{off}	power OFF leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	± 200	μ A
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	200	μ A
ΔI_{CC}	additional quiescent supply current per pin	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	-	5000	μ A

[1] Typical values are measured at maximum V_{CC} and $T_{amb} = 25$ °C.

12. Dynamic characteristics

Table 10: Dynamic characteristics

$GND = 0 V$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1]							
t_{PHL} , t_{PLH}	propagation delay A, B, C to Y	see Figure 11 and 12					
		$V_{CC} = 1.65 V$ to $1.95 V$	1.0	6.0	14.4	ns	
		$V_{CC} = 2.3 V$ to $2.7 V$	0.5	3.5	8.3	ns	
		$V_{CC} = 2.7 V$	0.5	4.2	8.5	ns	
		$V_{CC} = 3.0 V$ to $3.6 V$	0.5	3.8	6.3	ns	
		$V_{CC} = 4.5 V$ to $5.5 V$	0.5	3.0	5.1	ns	
C_{PD}	power dissipation capacitance per buffer	$V_{CC} = 3.3 V$	[2] [3]	-	20	-	pF
$T_{amb} = -40\text{ °C to }+125\text{ °C}$							
t_{PHL} , t_{PLH}	propagation delay A, B, C to Y	see Figure 11 and 12					
		$V_{CC} = 1.65 V$ to $1.95 V$	1.0	-	18	ns	
		$V_{CC} = 2.3 V$ to $2.7 V$	0.5	-	10.4	ns	
		$V_{CC} = 2.7 V$	0.5	-	10.6	ns	
		$V_{CC} = 3.0 V$ to $3.6 V$	0.5	-	7.9	ns	
		$V_{CC} = 4.5 V$ to $5.5 V$	0.5	-	6.4	ns	

[1] Typical values are measured at nominal V_{CC} and $T_{amb} = 25\text{ °C}$.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[3] The condition is $V_I = GND$ to V_{CC} .

13. Waveforms

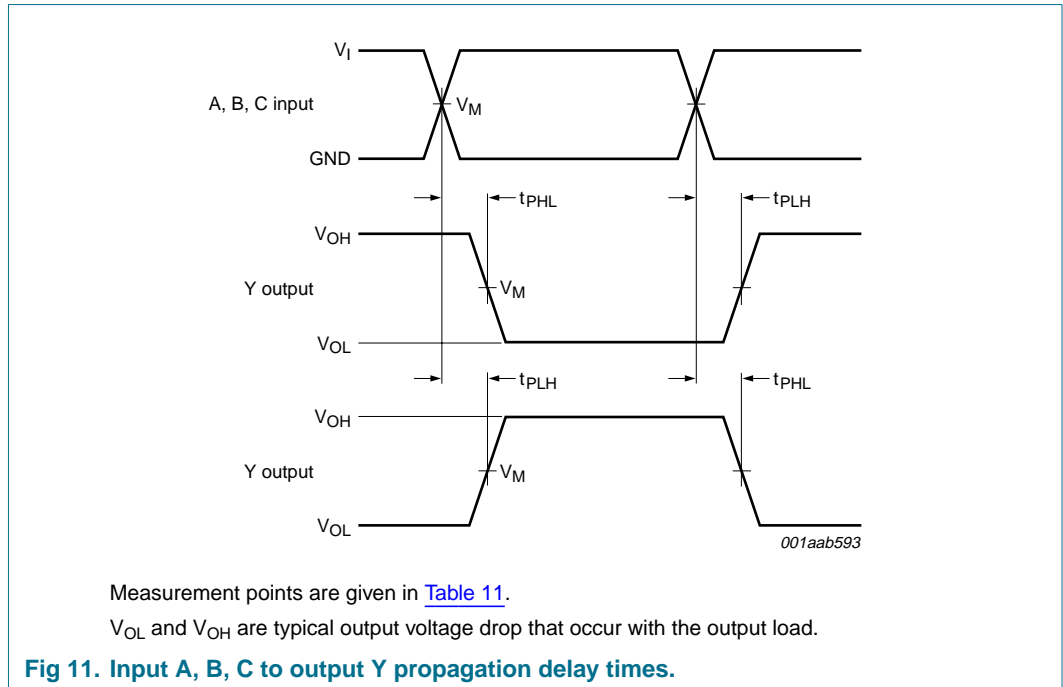


Table 11: Measurement points

Supply voltage	Input		Output
V_{CC}	V_M	V_I	V_M
1.65 V to 1.95 V	$0.5 \times V_{CC}$	V_{CC}	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	V_{CC}	$0.5 \times V_{CC}$
2.7 V	1.5 V	2.7 V	1.5 V
3.0 V to 3.6 V	1.5 V	2.7 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	V_{CC}	$0.5 \times V_{CC}$

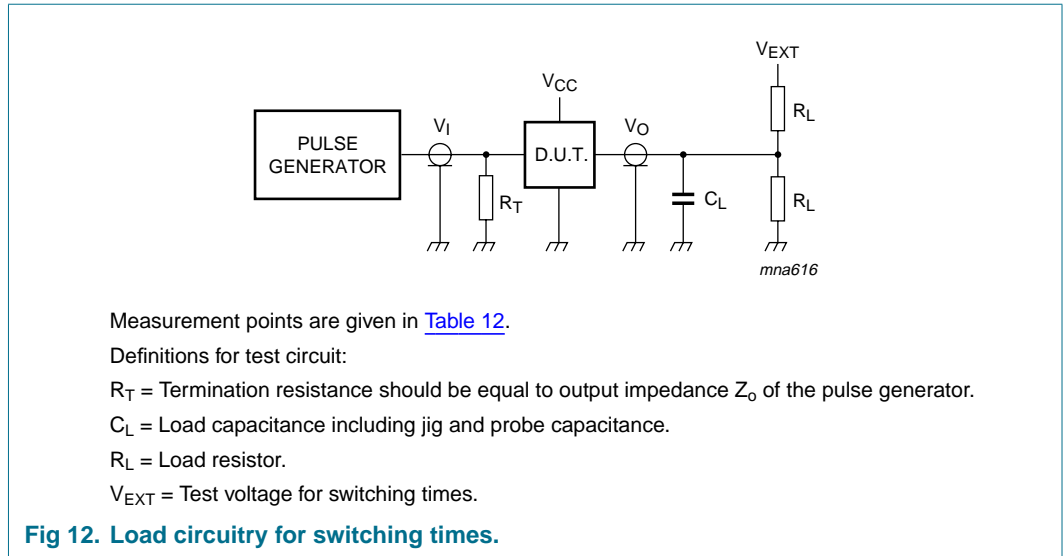


Table 12: Measurement points

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	$t_r = t_f$	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open	GND	$2 \times V_{CC}$
2.3 to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

14. Transfer characteristics

Table 13: Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40$ °C to $+85$ °C [1]						
V_{T+}	positive-going threshold voltage	see Figure 13 , 14 , 15 and 16				
		$V_{CC} = 1.8$ V	0.70	1.02	1.20	V
		$V_{CC} = 2.3$ V	1.11	1.42	1.60	V
		$V_{CC} = 3.0$ V	1.50	1.79	2.00	V
		$V_{CC} = 4.5$ V	2.16	2.52	2.74	V
		$V_{CC} = 5.5$ V	2.61	2.99	3.33	V
V_{T-}	negative-going threshold voltage	see Figure 13 , 14 , 15 and 16				
		$V_{CC} = 1.8$ V	0.30	0.53	0.72	V
		$V_{CC} = 2.3$ V	0.58	0.77	1.00	V
		$V_{CC} = 3.0$ V	0.80	1.04	1.30	V
		$V_{CC} = 4.5$ V	1.21	1.55	1.90	V
		$V_{CC} = 5.5$ V	1.45	1.86	2.29	V

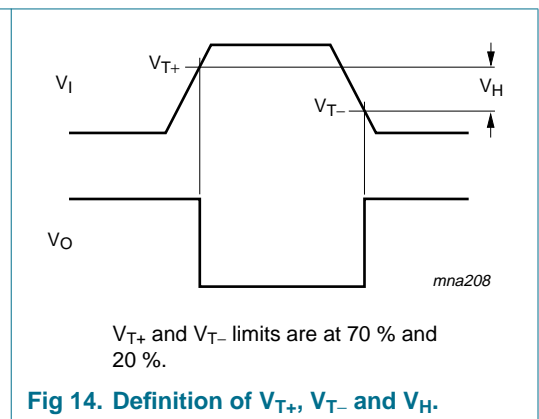
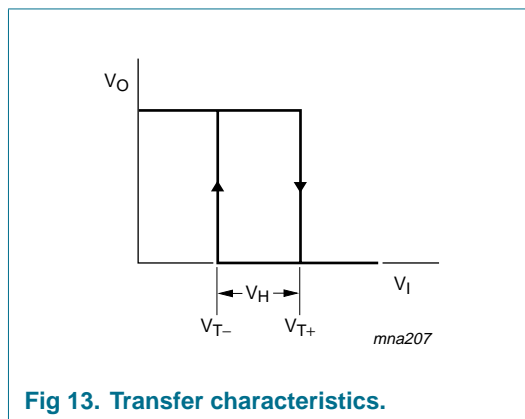
Table 13: Transfer characteristics ...continued

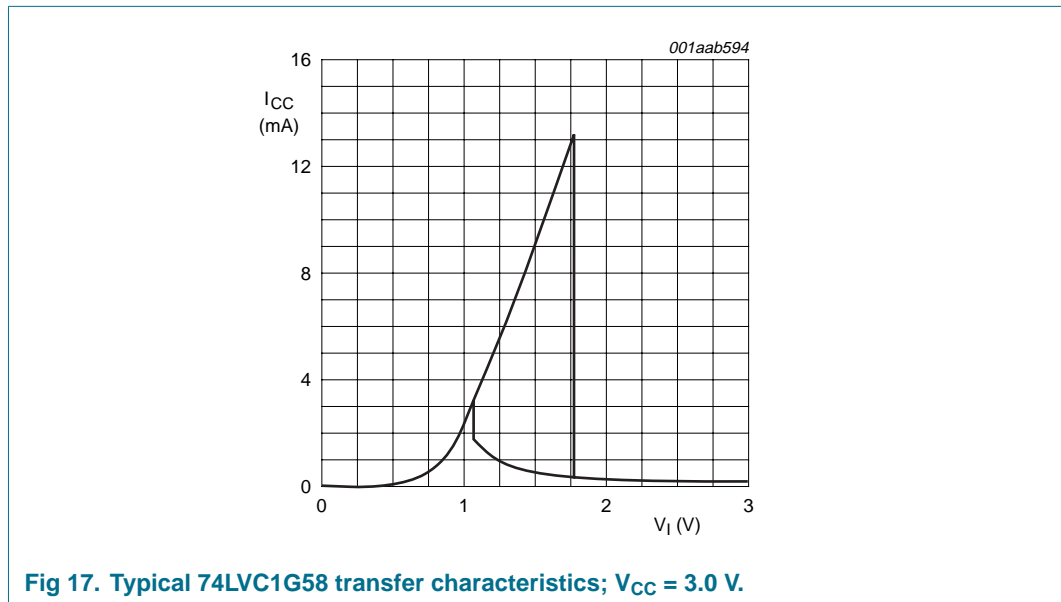
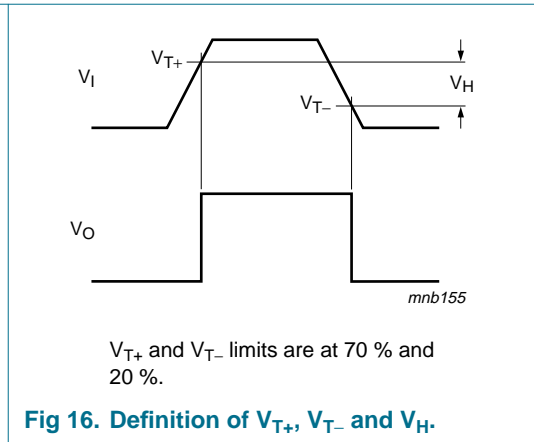
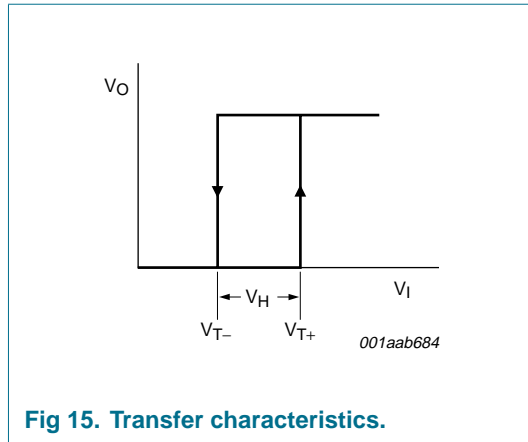
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_H	hysteresis voltage ($V_{T+} - V_{T-}$)	see Figure 13 , 14 , 15 and 16				
		$V_{CC} = 1.8\text{ V}$	0.30	0.48	0.62	V
		$V_{CC} = 2.3\text{ V}$	0.40	0.64	0.80	V
		$V_{CC} = 3.0\text{ V}$	0.50	0.75	1.00	V
		$V_{CC} = 4.5\text{ V}$	0.71	0.97	1.20	V
		$V_{CC} = 5.5\text{ V}$	0.71	1.13	1.40	V
$T_{amb} = -40\text{ °C to }+125\text{ °C}$						
V_{T+}	positive-going threshold voltage	see Figure 13 , 14 , 15 and 16				
		$V_{CC} = 1.8\text{ V}$	0.67	-	1.20	V
		$V_{CC} = 2.3\text{ V}$	1.08	-	1.60	V
		$V_{CC} = 3.0\text{ V}$	1.47	-	2.00	V
		$V_{CC} = 4.5\text{ V}$	2.13	-	2.74	V
		$V_{CC} = 5.5\text{ V}$	2.58	-	3.33	V
V_{T-}	negative-going threshold voltage	see Figure 13 , 14 , 15 and 16				
		$V_{CC} = 1.8\text{ V}$	0.30	-	0.75	V
		$V_{CC} = 2.3\text{ V}$	0.58	-	1.03	V
		$V_{CC} = 3.0\text{ V}$	0.80	-	1.33	V
		$V_{CC} = 4.5\text{ V}$	1.21	-	1.93	V
		$V_{CC} = 5.5\text{ V}$	1.45	-	2.32	V
V_H	hysteresis voltage ($V_{T+} - V_{T-}$)	see Figure 13 , 14 , 15 and 16				
		$V_{CC} = 1.8\text{ V}$	0.23	-	0.62	V
		$V_{CC} = 2.3\text{ V}$	0.34	-	0.80	V
		$V_{CC} = 3.0\text{ V}$	0.44	-	1.00	V
		$V_{CC} = 4.5\text{ V}$	0.65	-	1.20	V
		$V_{CC} = 5.5\text{ V}$	0.65	-	1.40	V

[1] Typical values are measured at $T_{amb} = 25\text{ °C}$.

15. Waveforms transfer characteristics





16. Package outline

Plastic surface mounted package; 6 leads

SOT363

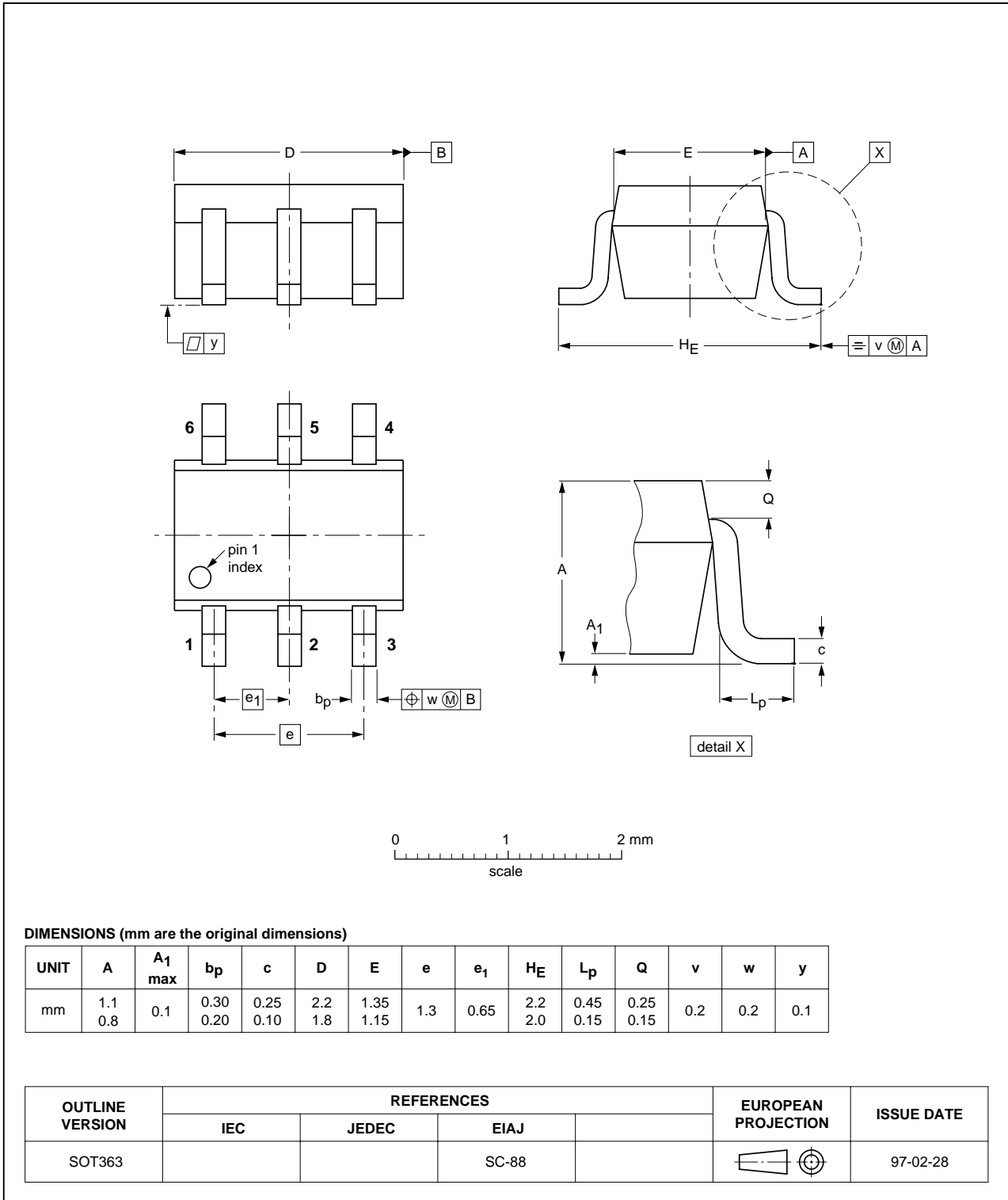


Fig 18. Package outline SOT363 (SC-88).

Plastic surface mounted package; 6 leads

SOT457

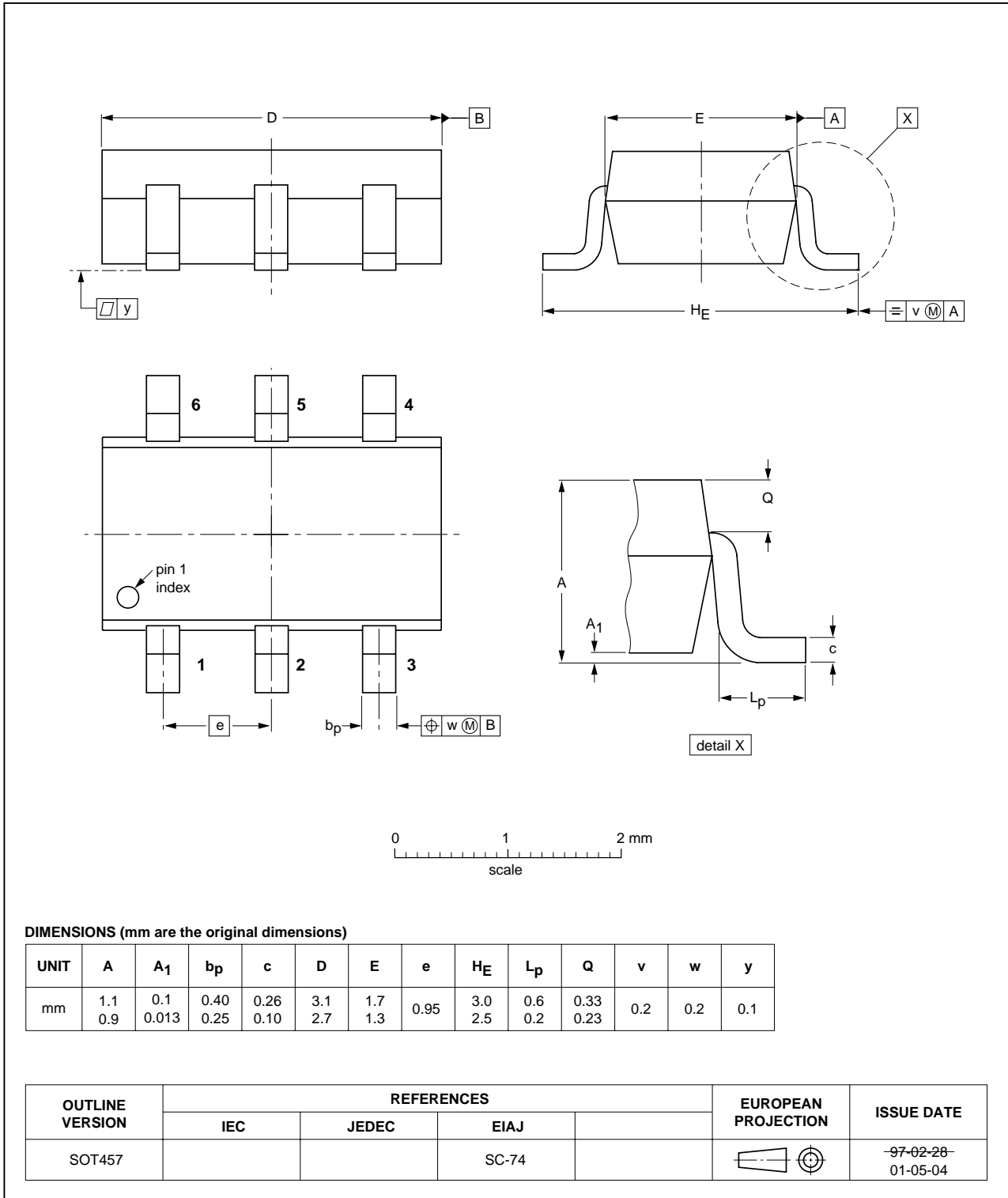


Fig 19. Package outline SOT457 (SC-74).

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

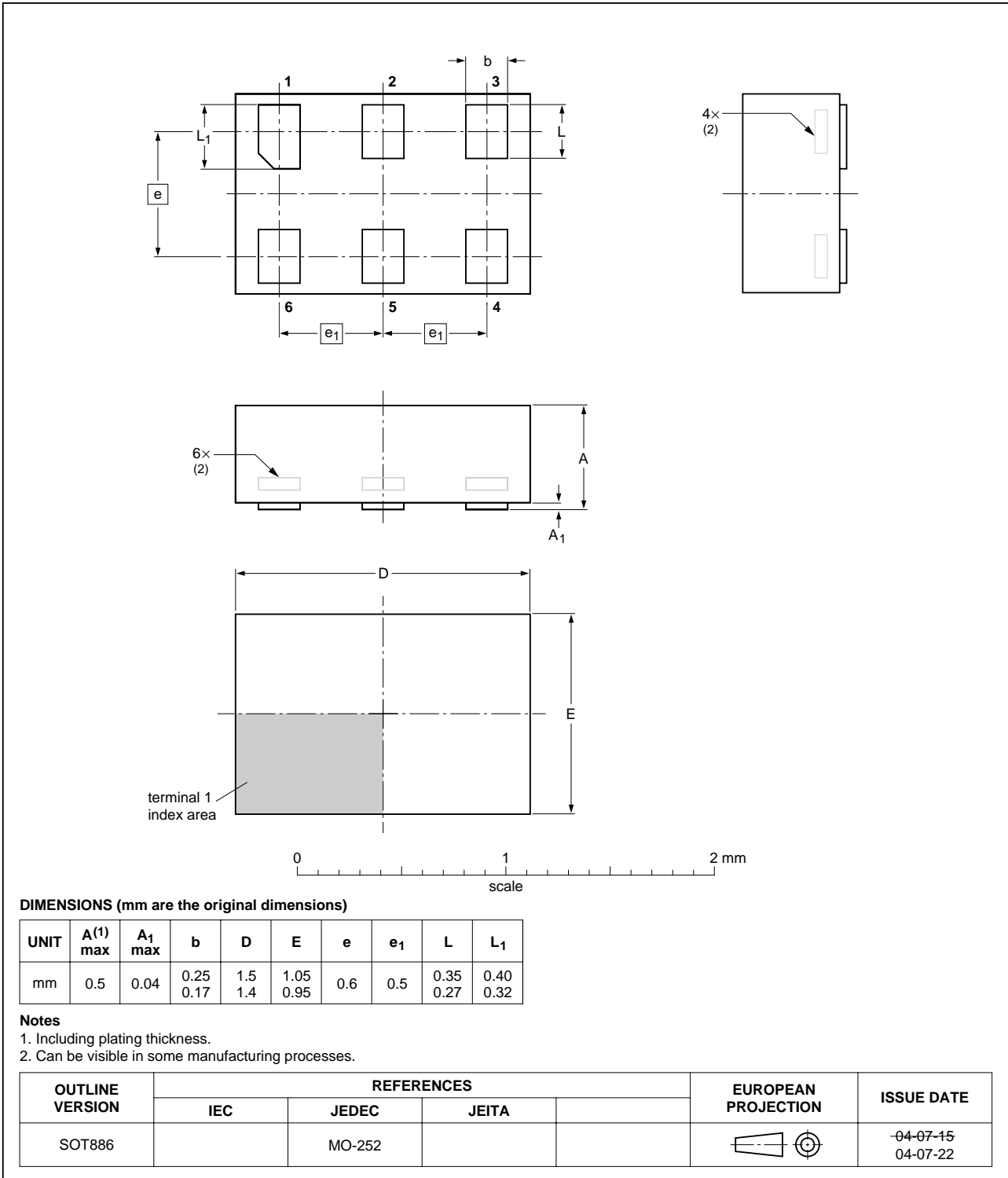


Fig 20. Package outline SOT886 (XSON6).

17. Revision history

Table 14: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74LVC1G58_1	20040915	Product data sheet	-	9397 750 13852	-

18. Data sheet status

Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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